



TO-92MOD Plastic-Encapsulate Transistors

KSA910 TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 0.8 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -0.05 A

Collector-base voltage

$V_{(BR)CBO}$: -150 V

Operating and storage junction temperature range

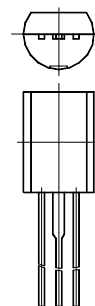
T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

TO-92MOD

1. EMITTER

2. COLLECTOR

3. BASE



123

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-150			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -5mA, I_B = 0$	-150			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -150V, I_E = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -5V, I_C = -10mA$	40		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10mA, I_B = -1mA$			-0.8	V
Transition frequency	f_T	$V_{CE} = -30V, I_C = -10mA$	80			MHz

CLASSIFICATION OF h_{FE}

Rank	R	O	Y
Range	40-80	70-140	120-240